

C4D02120A–Silicon Carbide Schottky Diode

Z-REC™ RECTIFIER

$$V_{RRM} = 1200 \text{ V}$$

$$I_F = 2 \text{ A}$$

$$Q_c = 15 \text{ nC}$$

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives

Package



TO-220-2



Part Number	Package	Marking
C4D02120A	TO-220-2	C4D02120

Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_R	DC Peak Reverse Voltage	1200	V		
$I_{F(AVG)}$	Maximum DC Current	5.9	A	$T_c=135^\circ\text{C}$, no AC component	
I_{FRM}	Repetitive Peak Forward Surge Current	13 8.4	A	$T_c=25^\circ\text{C}$, $t_p=10 \text{ ms}$, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10 \text{ ms}$, Half Sine Pulse	
I_{FSM}	Non-Repetitive Forward Surge Current	19 16.5	A	$T_c=25^\circ\text{C}$, $t_p=10 \text{ ms}$, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10 \text{ ms}$, Half Sine Pulse	
P_{tot}	Power Dissipation	40.5 17.6	W	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	
T_c	Maximum Case Temperature	135	$^\circ\text{C}$		
T_j	Operating Junction Range	-55 to +175	$^\circ\text{C}$		
T_{stg}	Storage Temperature Range	-55 to +135	$^\circ\text{C}$		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.4 1.9	1.8 3	V	$I_F = 2\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 2\text{ A}$ $T_J = 175^\circ\text{C}$	
I_R	Reverse Current	10 40	50 150	μA	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	15		nC	$V_R = 1200\text{ V}$, $I_F = 2\text{ A}$ $di/dt = 200\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	167 11 8		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 800\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	3.7		$^\circ\text{C}/\text{W}$		

Typical Performance

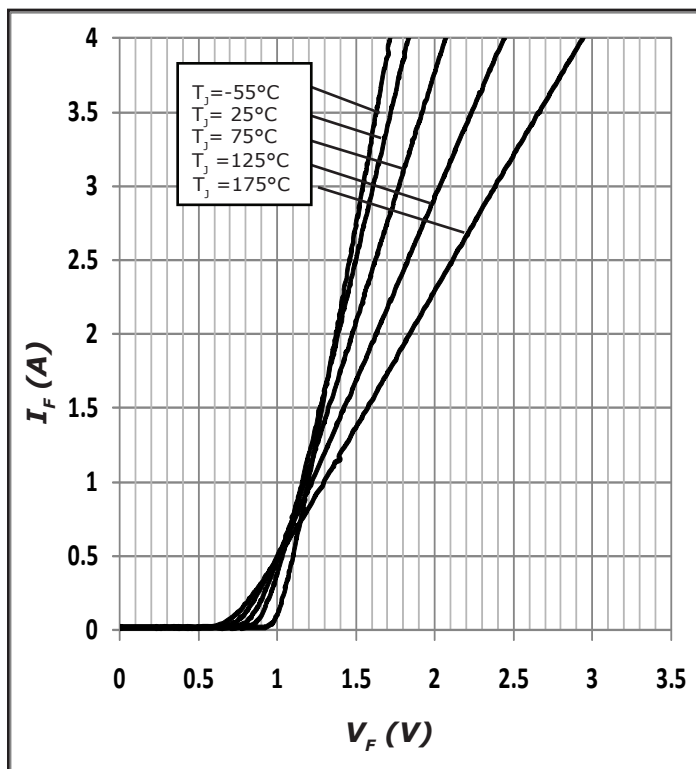


Figure 1. Forward Characteristics

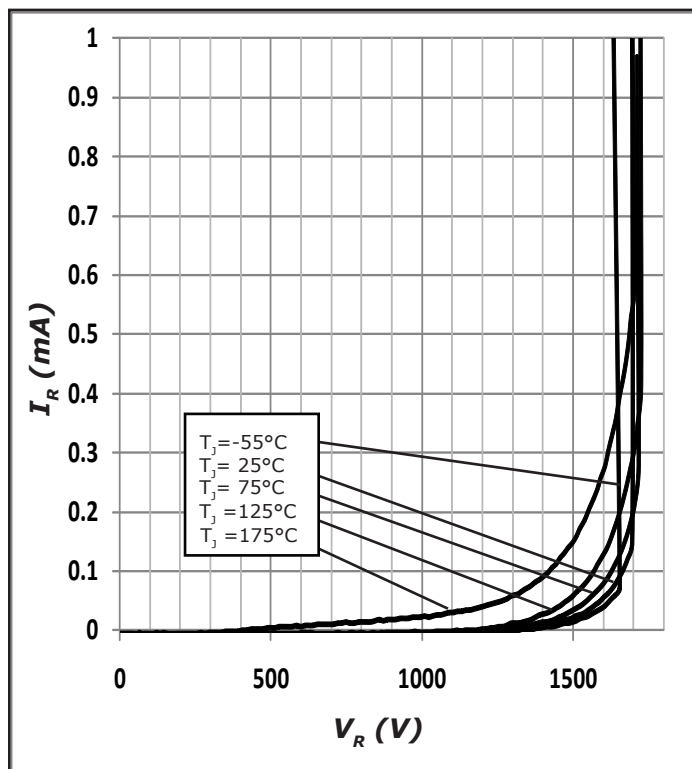


Figure 2. Reverse Characteristics

Typical Performance

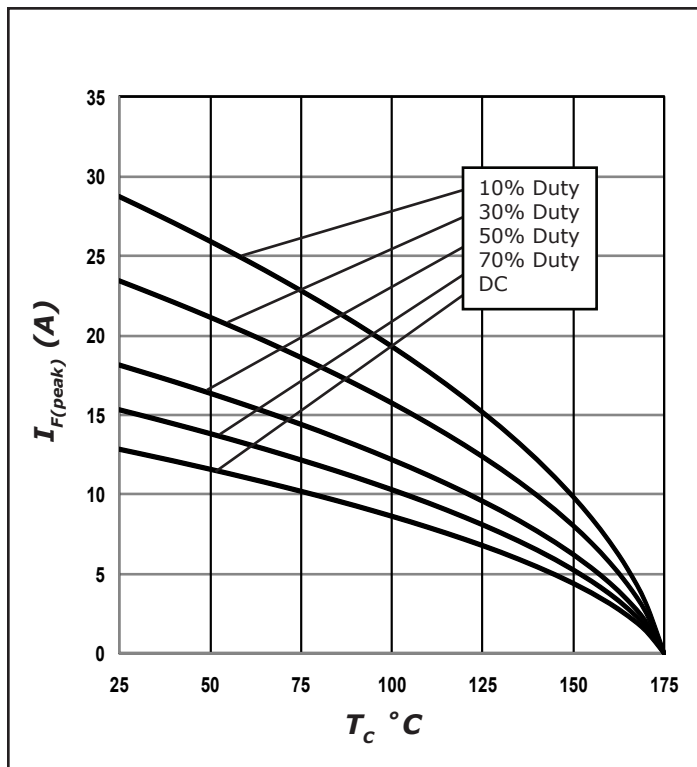


Figure 3. Current Derating

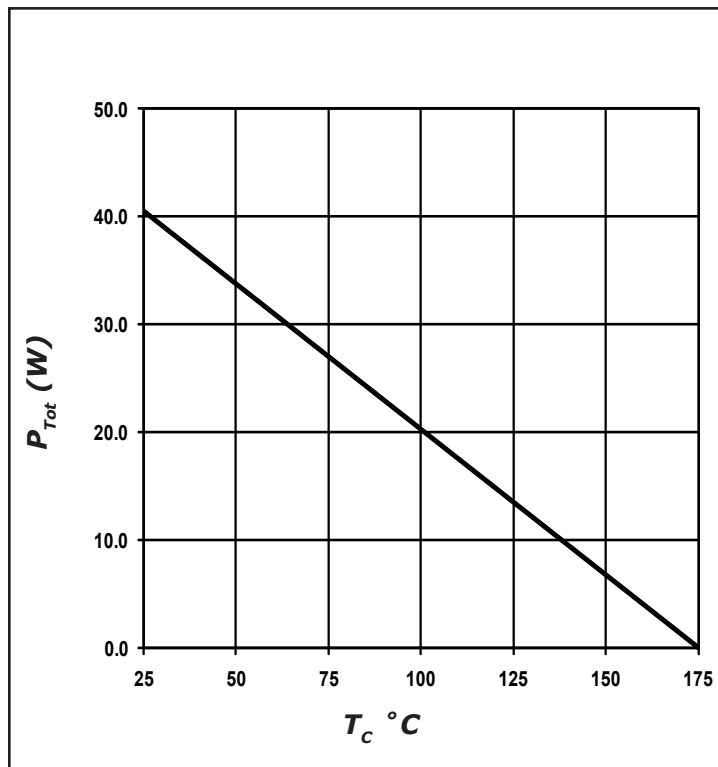


Figure 4. Power Derating

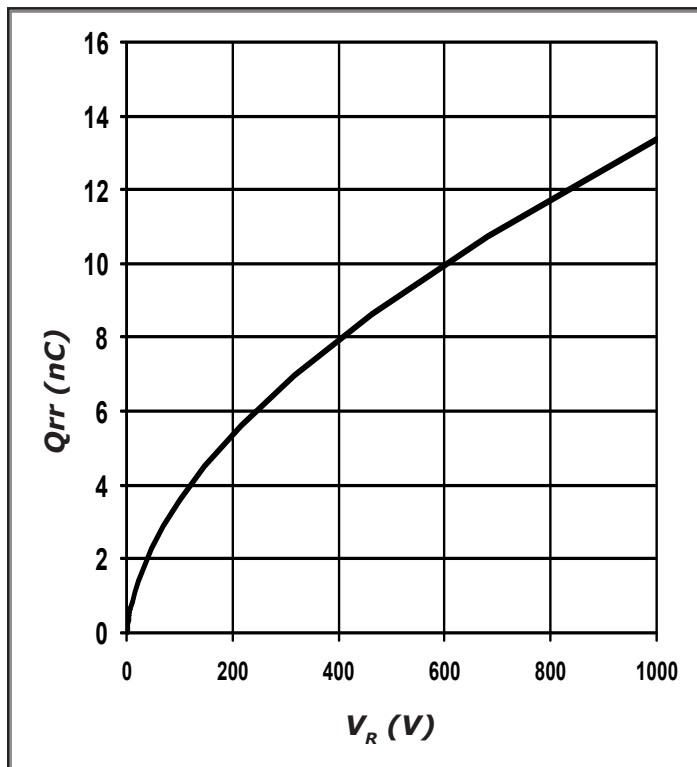


Figure 5. Recovery Charge vs. Reverse Voltage

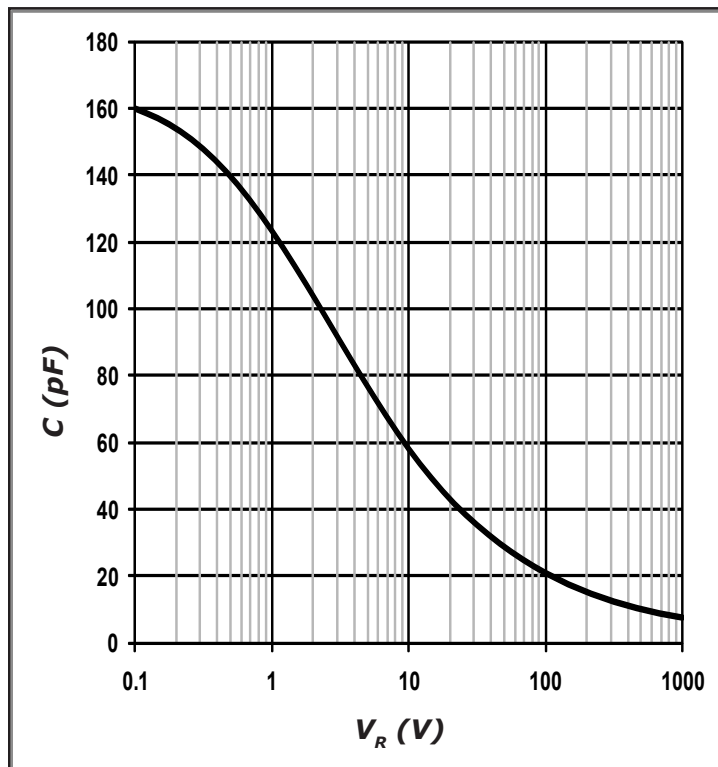


Figure 6. Capacitance vs. Reverse Voltage

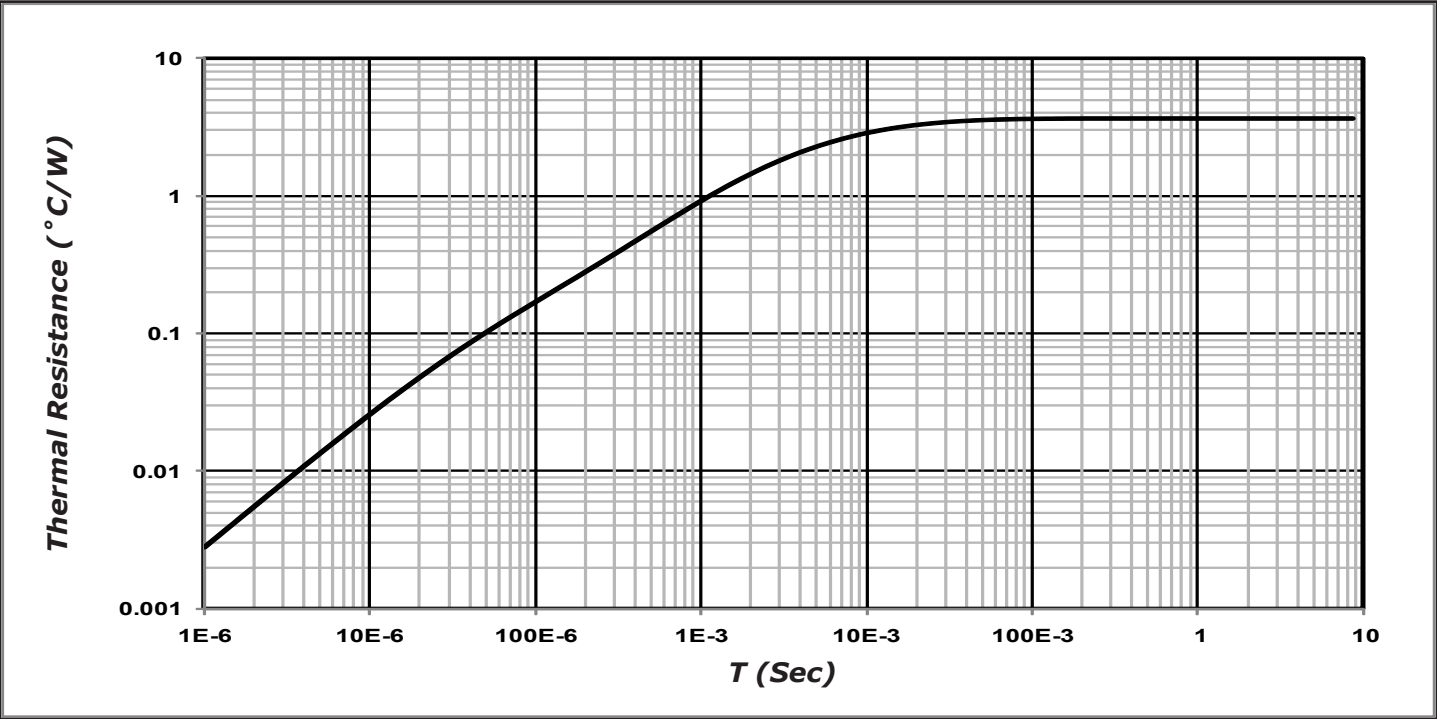
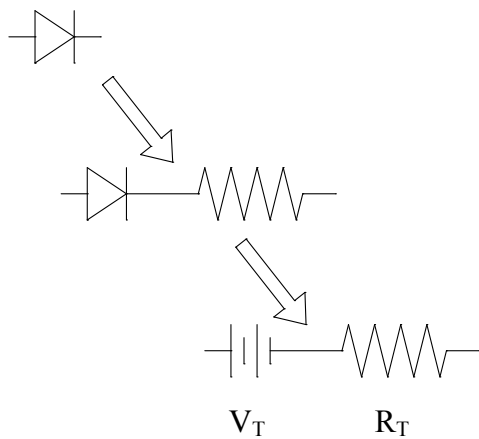


Figure 7. Transient Thermal Impedance

Diode Model



$$V_{fT} = V_T + I_f \cdot R_T$$

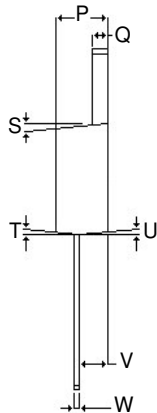
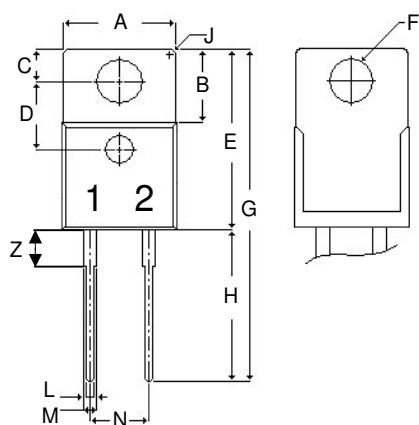
$$V_T = 0.99 + (T_j \cdot -1.70 \cdot 10^{-3})$$

$$R_T = 0.15 + (T_j \cdot 2.40 \cdot 10^{-4})$$

Note: T_j = Diode Junction Temperature In Degrees Celcius

Package Dimensions

Package TO-220-2

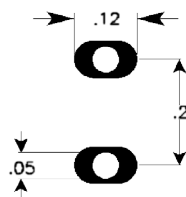


POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.381	.410	9.677	10.414
B	.235	.255	5.969	6.477
C	.100	.120	2.540	3.048
D	.223	.337	5.664	8.560
E	.590	.615	14.986	15.621
F	.143	.153	3.632	3.886
G	1.105	1.147	28.067	29.134
H	.500	.550	12.700	13.970
J	R 0.197		R 0.197	
L	.025	.036	.635	.914
M	.045	.055	1.143	1.397
N	.195	.205	4.953	5.207
P	.165	.185	4.191	4.699
Q	.048	.054	1.219	1.372
S	3°	6°	3°	6°
T	3°	6°	3°	6°
U	3°	6°	3°	6°
V	.094	.110	2.388	2.794
W	.014	.025	.356	.635
X	3°	5.5°	3°	5.5°
Y	.385	.410	9.779	10.414
Z	.130	.150	3.302	3.810

NOTE:

1. Dimension L, M, W apply for Solder Dip Finish

Recommended Solder Pad Layout



TO-220-2

Part Number	Package	Marking
C4D02120A	TO-220-2	C4D02120

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